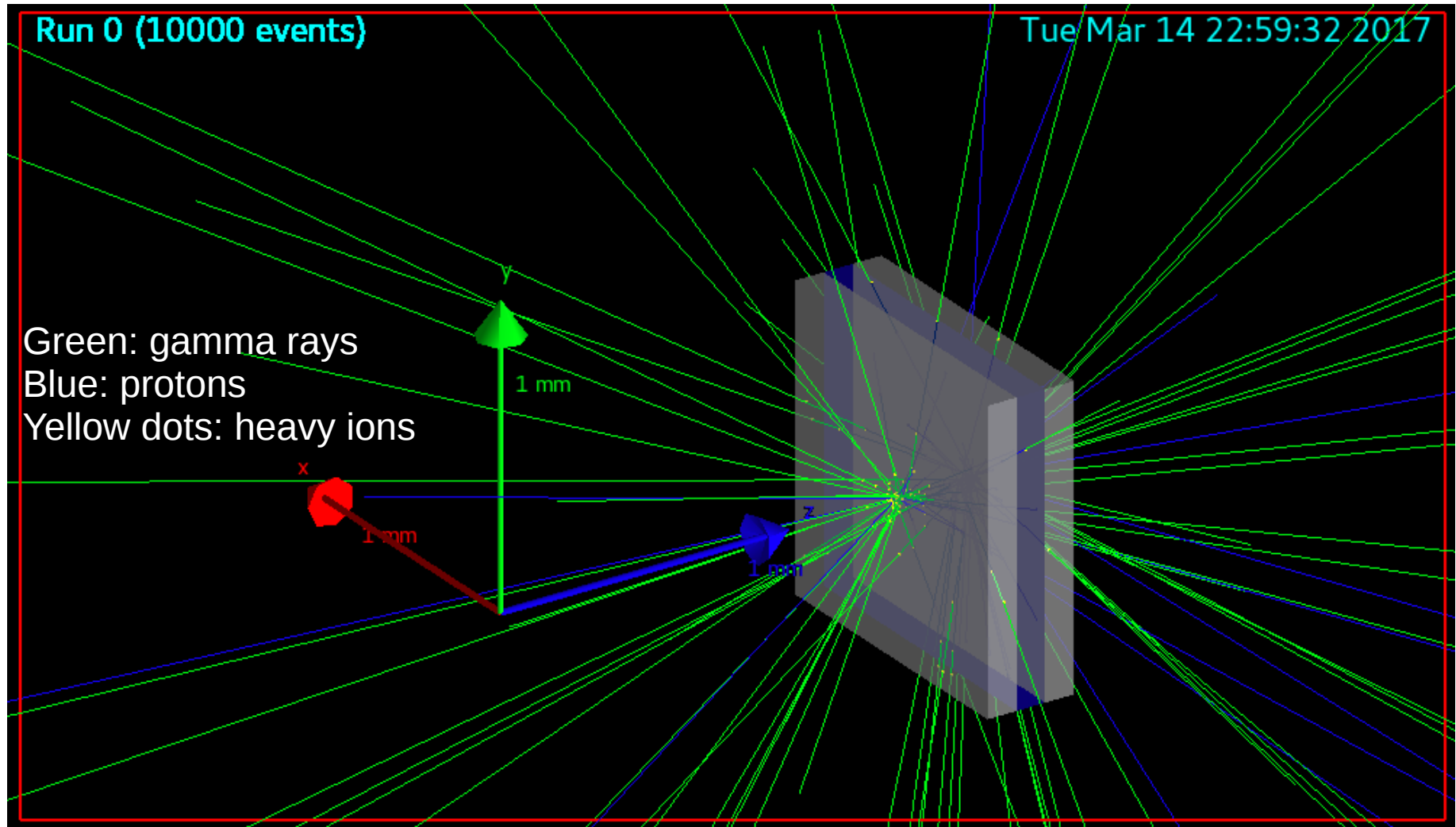


# SEU Detector Update

Ray Xu  
Mar 17, 2017

- Incident particle: fast neutrons  $> 20$  MeV
- Neutrons only interact inelastically @ these energies
  - Produces 2ndary particles through “catastrophic” collisions with chip nuclei
  - These 2ndary particles can cause SEU’s via linear energy transfer (LET)
  - ... Also what we want to detect to coincide with SEU’s
- Conclusion: optimize detector for the 2ndary, ionizing particles

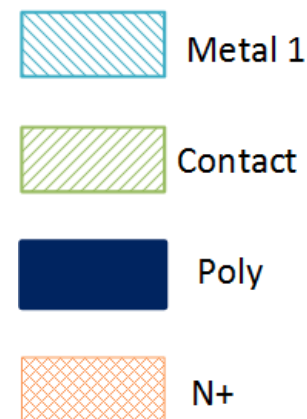
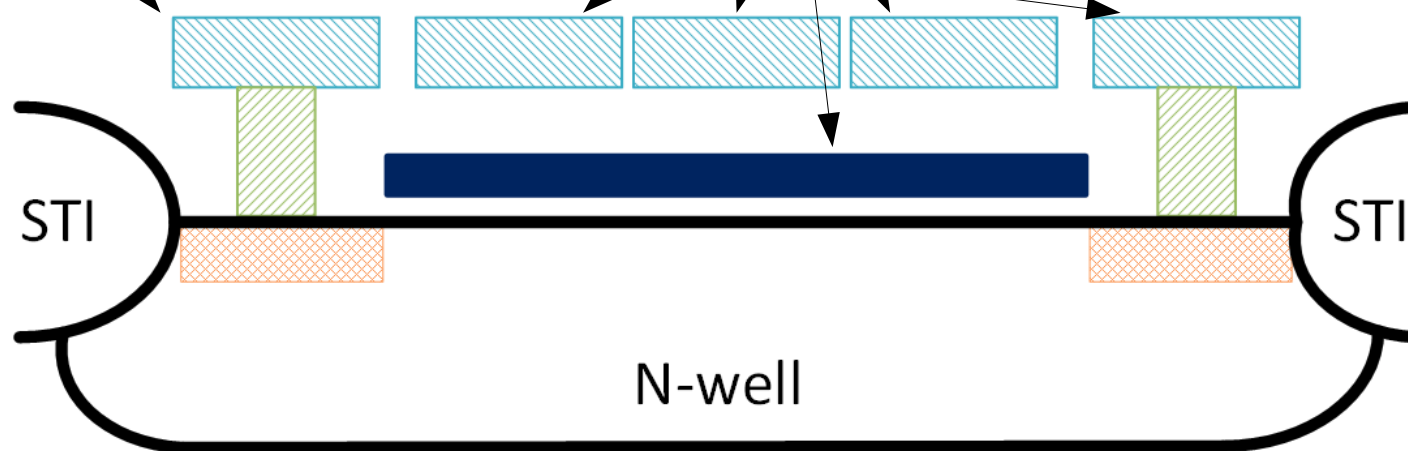


- 1mm x 1mm parallel-plate capacitor (Cu and SiO<sub>2</sub>)
- Bombarded with 100 MeV neutrons (not shown)
- Most collisions occur with the metal
  - Makes sense; copper's nuclei is larger than SiO<sub>2</sub>
- At the least: gamma rays and additional neutrons are produced.
  - No LET → good! No SEU.
- At the most: aforementioned + protons, heavy ions of metal/Si/O, other heavy particles (alpha, deuterium, etc)
  - Protons: > 1 MeV
  - Heavy ions: < 1 MeV; < 1 um range
- TODO: Tweak maxStepLength to be able to simulate a more realistic-sized capacitor.

- NMOS varactor + M1 shield (to observe gamma rays by photoelectric/Compton scattering)
- 37 fF ( $\sim 1$  CDAC unit cap) – 270 fF

Goes to  
ground  
“MINUS”

High-Z node  
“PLUS”



“Length-wise” x-section view

- Major drawback to varactor structure
- Perturbed charge scales with amount of energy transfer, which scales with the “thickness” of the E-field region.
- LET in the thin oxide ( $\sim 2.6$  nm thick) will be very limited compared to MOM cap ( $\sim$ microns thick).
- Try M1-poly MOM cap?

- Assume: 2ndary particle of one 1MeV proton (conservative energy estimate) passes thru SiO<sub>2</sub> in the E-field of a MOM finger capacitor. How much perturbed charge?

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Density:  $\rho = 2.32 \text{ [g}\cdot\text{cm}^{-3}\text{]}$

LET @ 1 MeV in SiO<sub>2</sub>:  $\frac{1}{\rho} \frac{dE}{dx} = 189.8 \text{ [MeV}\cdot\text{cm}^2\cdot\text{g}^{-1}\text{ ]}$

$$\Rightarrow \frac{dE}{dx} = 44.03 \text{ [keV}\cdot\mu\text{m}^{-1}\text{]}$$



- Assume: 2ndary particle of one 1MeV proton (conservative energy estimate) passes thru SiO<sub>2</sub> in the E-field of a MOM finger capacitor. How much perturbed charge?

Ion pair generation energy:  $w = 17 \text{ [eV]}$

Charge of ion pair:  $q_E = 1.6 \cdot 10^{-19} \text{ [C]} \Rightarrow \frac{q_E}{w} = 9.41 \cdot 10^{-21} \text{ [C} \cdot \text{eV}^{-1}]$

Thickness of M1-PO:  $t \approx 0.5 \text{ [}\mu\text{m]} \Rightarrow dE \approx 22.02 \text{ [keV]}$

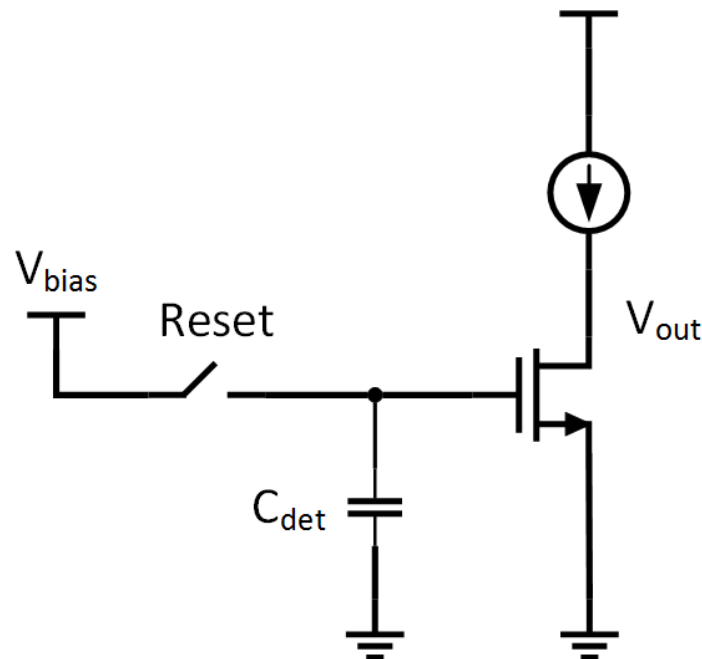
$$\Rightarrow \Delta Q = \frac{q_E}{w} \cdot dE \approx 0.21 \text{ [fC]}$$

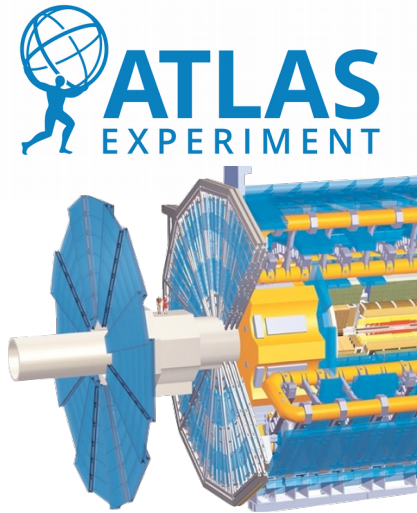
Compared to thickness of gate oxide of a few nano-meters:

$dE \sim \text{[eV]}; \Delta Q \sim \text{[aC]}$

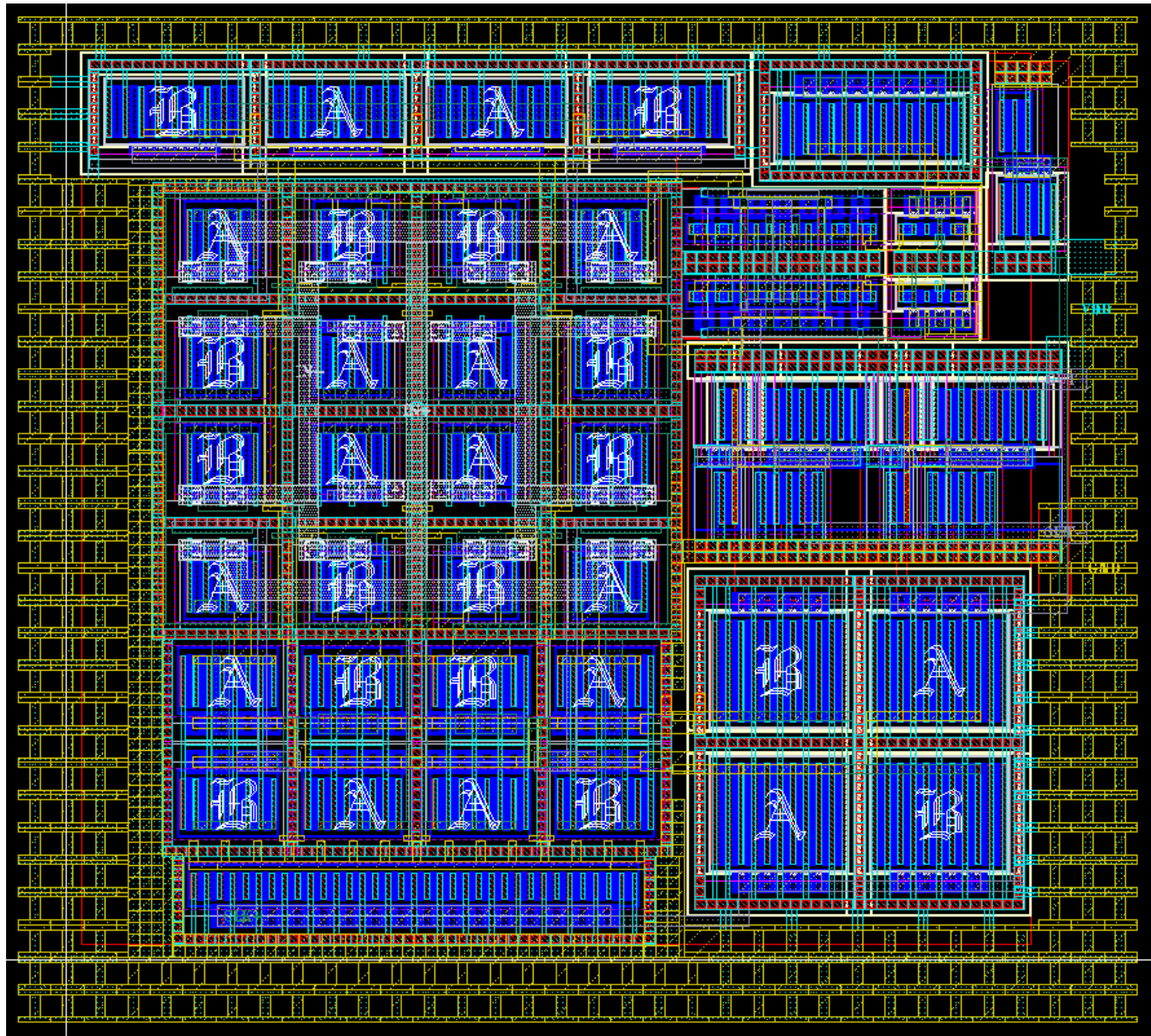
- M1-PO MOM finger cap of dimensions equal to a CDAC unit cap cell has extracted capacitance of ~20 fF.
- $\Delta Q$  Should yield a 10mV perturbation of capacitor voltage if detector capacitor initially charged to half-VDD (600mV)
- Slight problem: dielectric between M1-PO is some “mystery dielectric” with lower  $\epsilon_r$
- But, LET should be on the same order of magnitude...

- “Electrometer”
- $C_{gg} \ll C_{det}$
- Reset sync'd to sampling clock
- one per detector cap + reference
- TODO: determine BW, noise, and sw. leakage requirement



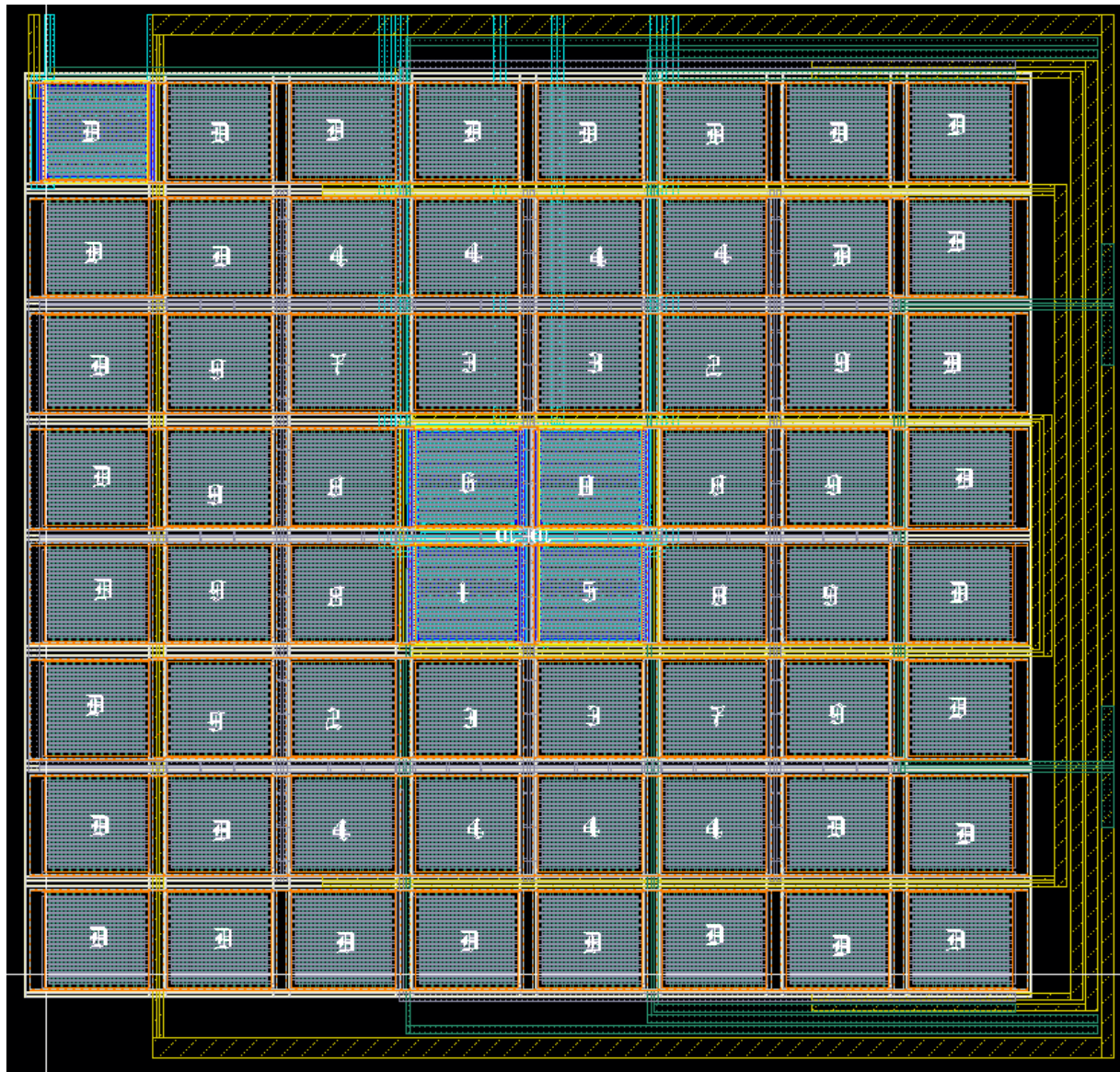


# Layout Update

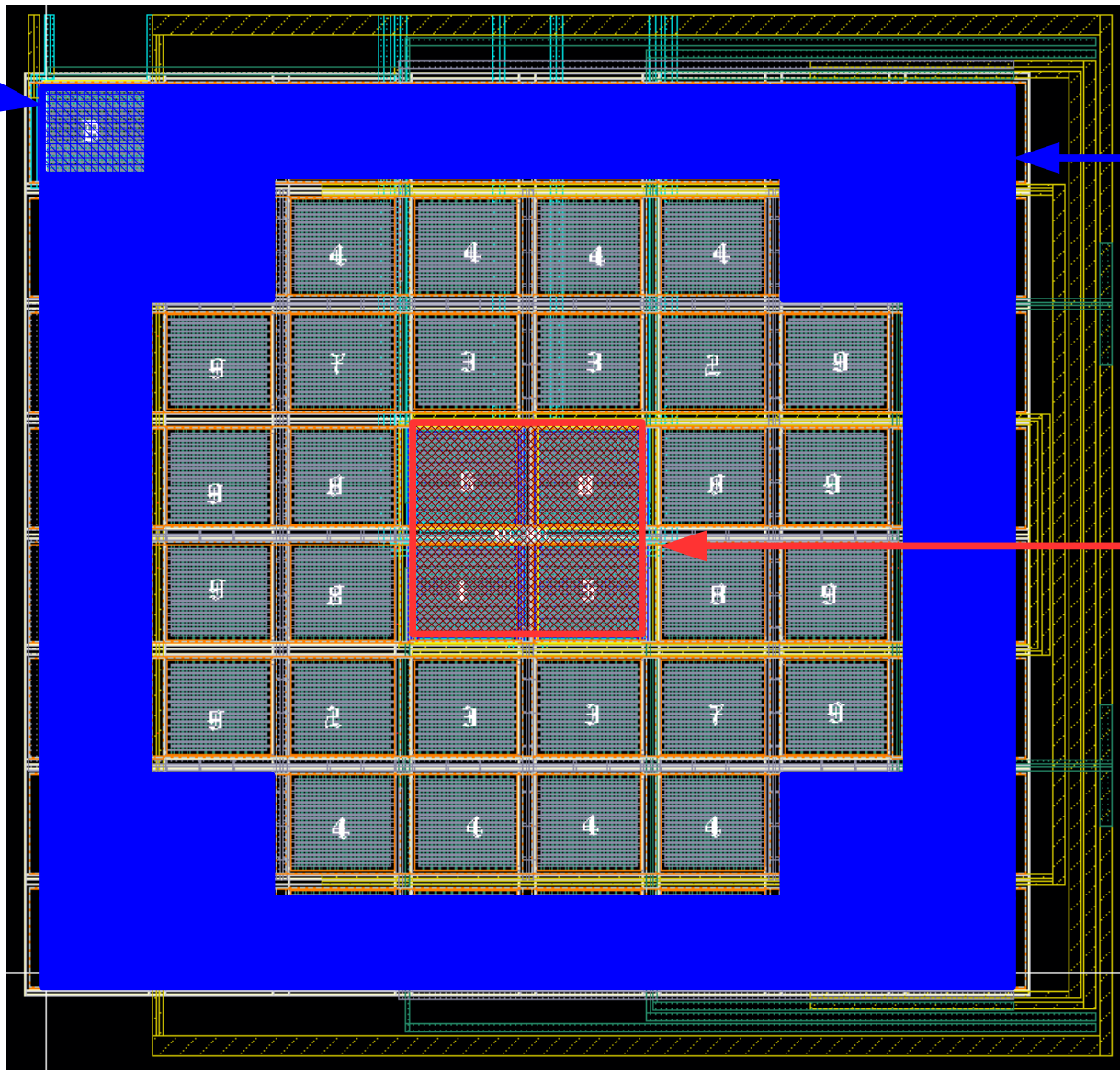


- Finalized for 1p6m 3X1Z1U
- Approx 20  $\mu\text{m}$  x 20  $\mu\text{m}$
- Common-centroid, taking into account WPE and LOD
- Noise + (systematic) offset < 400  $\mu\text{V}$
- Worst-case  $t_{pd}$ :  $\Delta V_{\text{in}} = 400\mu\text{V} \rightarrow t_{pd} \approx 300 \text{ pS}$
- Power consumption @ 320 MHz clock: 200  $\mu\text{W}$  (?!?!)





MOM cap +  
MOSCAP  
detector  
(test struct)



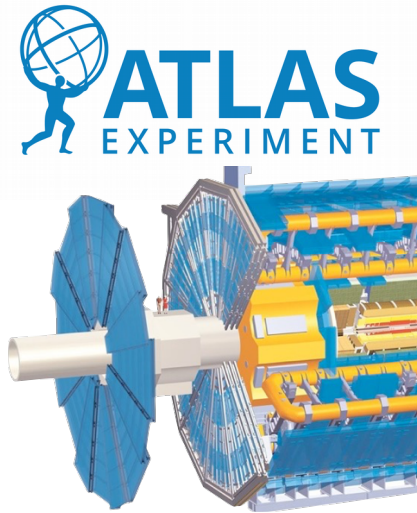
Dummy caps

4 CDAC unit  
caps + MOSCAP  
detector



- Approx 50  $\mu\text{m}$  x 50  $\mu\text{m}$
- All routing done inter-metal-stack (metals 2-4)
- “Alternating” metal routing to reduce uneven parasitics
- Do not use metal 5 (thick metal and copper x-s is larger than  $\text{SiO}_2$ )
- Metal 1 reserved for detector structures
- Parasitic extraction: all cap ratios within 1-2 fF of unit cap
- TODO: Replace MOSCAP with M1-PO MOM detector structure

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- [1] <http://holbert.faculty.asu.edu/eee460/IonizationRange.pdf>
  - [2] PSTAR database [http://physics.nist.gov/cgi-bin/Star/ap\\_table.pl](http://physics.nist.gov/cgi-bin/Star/ap_table.pl)



# Backup Slides

